**Preferred Device** 

# **Dual Schottky Barrier Diodes**

Application circuit designs are moving toward the consolidation of device count and into smaller packages. The new SOT-363 package is a solution which simplifies circuit design, reduces device count, and reduces board space by putting two discrete devices in one small six-leaded package. The SOT-363 is ideal for low-power surface mount applications where board space is at a premium, such as portable products.

### **Surface Mount Comparisons:**

	SOT-363	SOT-23
Area (mm²)	4.6	7.6
Max Package P <sub>D</sub> (mW)	120	225
Device Count	2	1

## **Space Savings:**

Package	1 × SOT-23	$2  imes  extsf{SOT-23}$	
SOT-363	40%	70%	

The MBD110DW, MBD330DW, and MBD770DW devices are spin-offs of our popular MMBD101LT1, MMBD301LT1, and MMBD701LT1 SOT-23 devices. They are designed for high-efficiency UHF and VHF detector applications. Readily available to many other fast switching RF and digital applications.

# Features

- Extremely Low Minority Carrier Lifetime
- Very Low Capacitance
- Low Reverse Leakage
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### **MAXIMUM RATINGS**

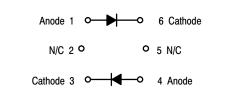
Rating		Symbol	Value	Unit
Reverse Voltage	MBD110DWT1G MBD330DWT1G MBD770DWT1G	V <sub>R</sub>	7.0 30 70	V
Forward Power Dissipation T <sub>A</sub> = 25°C		$P_{F}$	120	mW
Junction Temperature		TJ	-55 to +125	°C
Storage Temperature Range		T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



# ON Semiconductor®

#### http://onsemi.com





SC-88 / SOT-363 CASE 419B STYLE 6

### **MARKING DIAGRAM**



xx = Device Code

Refer to Ordering Table, page 2

M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

**Preferred** devices are recommended choices for future use and best overall value.

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

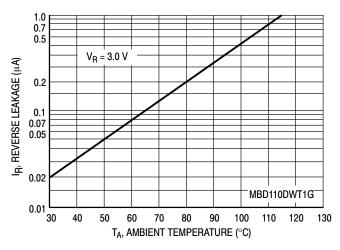
Characteristic		Symbol	Min	Тур	Max	Unit
Reverse Breakdown Voltage (I <sub>R</sub> = 10 μA)	MBD110DWT1G MBD330DWT1G MBD770DWT1G	V <sub>(BR)R</sub>	7.0 30 70	10 - -	- - -	V
Diode Capacitance (V <sub>R</sub> = 0, f = 1.0 MHz, Note 1)	MBD110DWT1G	C <sub>D</sub>	_	0.88	1.0	pF
Total Capacitance (V <sub>R</sub> = 15 Volts, f = 1.0 MHz) (V <sub>R</sub> = 20 Volts, f = 1.0 MHz)	MBD330DWT1G MBD770DWT1G	C <sub>T</sub>	- -	0.9 0.5	1.5 1.0	pF
Reverse Leakage (V <sub>R</sub> = 3.0 V) (V <sub>R</sub> = 25 V) (V <sub>R</sub> = 35 V)	MBD110DWT1G MBD330DWT1G MBD770DWT1G	I <sub>R</sub>	- - -	0.02 13 9.0	0.25 200 200	μΑ nA nA
Noise Figure (f = 1.0 GHz, Note 2)	MBD110DWT1G	NF	-	6.0	_	dB
Forward Voltage ( $I_F = 10 \text{ mA}$ ) ( $I_F = 1.0 \text{ mA}$ ) ( $I_F = 10 \text{ mA}$ ) ( $I_F = 1.0 \text{ mA}$ ) ( $I_F = 1.0 \text{ mA}$ )	MBD110DWT1G MBD330DWT1G MBD770DWT1G	V <sub>F</sub>	- - - -	0.5 0.38 0.52 0.42 0.7	0.6 0.45 0.6 0.5 1.0	V

## **ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>	
MBD110DWT1G	M4	SC-88 / SOT-363 (Pb-Free)		
MBD330DWT1G	T4	SC-88 / SOT-363 (Pb-Free)	3000 Units / Tape & Reel	
MBD770DWT1G	H5	SC-88 / SOT-363 (Pb-Free)		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

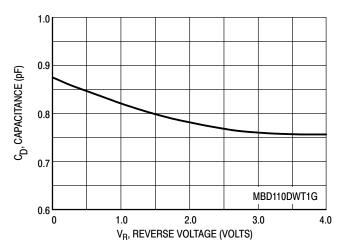
# TYPICAL CHARACTERISTICS MBD110DWT1G



100 T<sub>A</sub> = 85°C T<sub>A</sub> = -40°C T<sub>A</sub> = 25°C MBD110DWT1G 0.1 0.3 0.4 0.5 0.6 0.7 0.8 V<sub>F</sub> FORWARD VOLTAGE (VOLTS)

Figure 1. Reverse Leakage

Figure 2. Forward Voltage



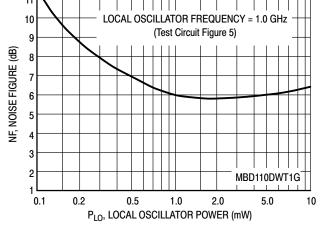


Figure 3. Capacitance

Figure 4. Noise Figure

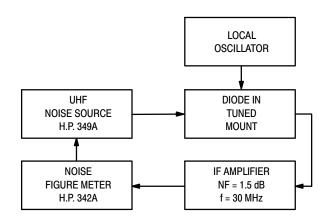
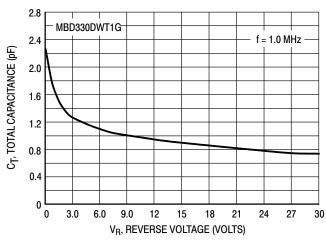


Figure 5. Noise Figure Test Circuit

### NOTES ON TESTING AND SPECIFICATIONS

- Note 1  $C_D$  and  $C_T$  are measured using a capacitance bridge (Boonton Electronics Model 75A or equivalent).
- Note 2 Noise figure measured with diode under test in tuned diode mount using UHF noise source and local oscillator (LO) frequency of 1.0 GHz. The LO power is adjusted for 1.0 mW. IF amplifier NF = 1.5 dB, f = 30 MHz, see
- Note 3 L<sub>S</sub> is measured on a package having a short instead of a die, using an impedance bridge (Boonton Radio Model 250A RX Meter).

# TYPICAL CHARACTERISTICS MBD330DWT1G



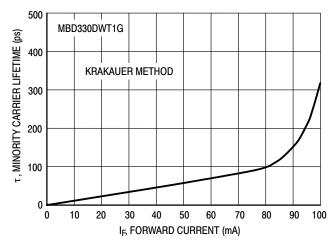
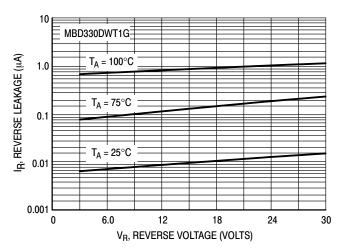


Figure 6. Total Capacitance

Figure 7. Minority Carrier Lifetime



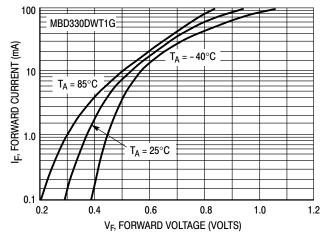
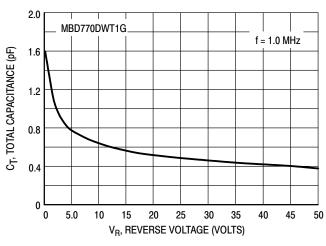


Figure 8. Reverse Leakage

Figure 9. Forward Voltage

# TYPICAL CHARACTERISTICS MBD770DWT1G



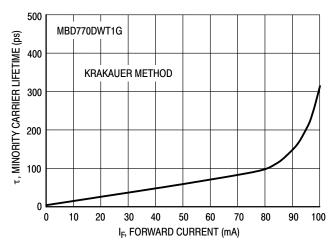
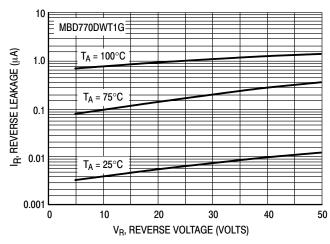


Figure 10. Total Capacitance

Figure 11. Minority Carrier Lifetime



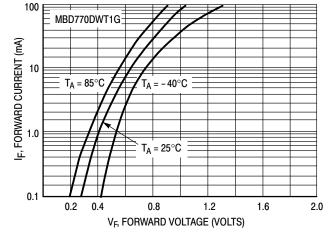
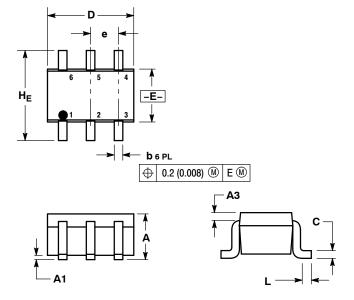


Figure 12. Reverse Leakage

Figure 13. Forward Voltage

### PACKAGE DIMENSIONS

SC-88 / SC-70 / SOT-363 CASE 419B-02 **ISSUE W** 



#### NOTES

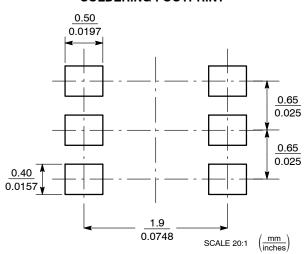
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982
- CONTROLLING DIMENSION: INCH.
- 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.95	1.10	0.031	0.037	0.043	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
А3		0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012	
С	0.10	0.14	0.25	0.004	0.005	0.010	
D	1.80	2.00	2.20	0.070	0.078	0.086	
Е	1.15	1.25	1.35	0.045	0.049	0.053	
е	0.65 BSC			0.026 BSC			
L	0.10	0.20	0.30	0.004	0.008	0.012	
HE	2.00	2.10	2.20	0.078	0.082	0.086	

# STYLE 6: PIN 1. ANODE 2

- 2
- N/C
- CATHODE 1 4. ANODE 1
- 6. CATHODE 2

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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